

Applications

- · Energy-Saving Light
- · Electronics Ballasts
- High Frequency Switching Power Supply
- High Frequency Power Transform and Commonly Power Amplifier

Features

• This product is available in AEC-Q101 Compliant and PPAP Capable also.

Absolute Maximum Ratings (Ta = 25°C Unless otherwise specified)

Parameter	Symbol	Value	Unit
Collector Emitter Voltage	Vces	800	
Collector Emitter Voltage	VCEO	450	V
Emitter Base Voltage	VEBO	9]
Collector Current (DC)	Ic	2	
Collector Current (Pulse)	Icp	4	
Base Current (DC)	Ів	1	A
Base Current (Pulse)	Івр	2]
Total Dissipation	Pc	50	W
Junction Temperature	TJ	150	°C
Storage Temperature	Тѕтс	-55 to +150]

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction to Case	Rth (j-c)	2.5	°C/W





Electrical Characteristics at (Ta = 25°C Unless otherwise specified)

Dorometer	Symbol Test Condition	Value		Unit		
Parameter	Symbol	rest Condition	Min.	Тур.	Max.	Unit
Collector Emitter Voltage	Vceo	Ic=10mA, I _B =0	450			
Collector Base Voltage	Vсво	Ic=1mA, I∈=0	800			V
Emitter Base Voltage	VEBO	I _E =1mA, I _C =0	9]		
Collector Cutoff Current	Ісво	Vcb=800V, IE=0			100	μА
Emitter Cutoff Current	Ієво	V _{EB} =9V, IC=0	<u></u>		10	
DC Commant Cain	h _{FE1}	Ic=500mA, VcE=5V	15]	25	
DC Current Gain	h _{FE2}	Ic=1A,VcE=5V	5]	25	
Callantan Funittan Catamatian Valtana	VCE(sat)	Ic=1A, Iв=0.25A]	0.5	
Collector Emitter Saturation Voltage		Ic=1.5A, Iв=0.5A			1	
Base Emitter Seturation Valtage	V _{BE} (sat)	IC=0.5A, IB=0.1A			1	V
Base Emitter Saturation Voltage		Ic=1A, Iв=0.25A]		1.2	
Integrated Diode Forward Voltage	VFEC	I _F =2A			2	
Turn On Time	ton	.,			1.1	
Fall Time	t f	Vcc=125V, Ic=1A, Iв1= -Iв2=0.2A.			0.7	μS
Storage Time	ts	101-102- 0.2 A,	2		4	
Transition Frequency	f⊤	Ic=100mA, VcE=10V	4			MHz

Note:

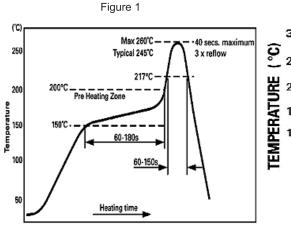
1. hFE Classification : 15-20 20-25

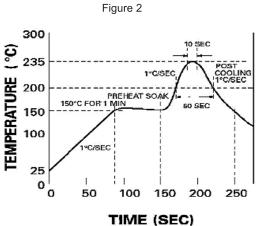
Recommended Reflow Solder Profiles

The recommended reflow solder profiles for Pb and Pb-free devices are shown below.

Figure 1 shows the recommended solder profile for devices that have Pb-free terminal plating, and where a Pb-free solder is used.

Figure 2 shows the recommended solder profile for devices with Pb-free terminal plating used with leaded solder, or for devices with leaded terminal plating used with a leaded solder.









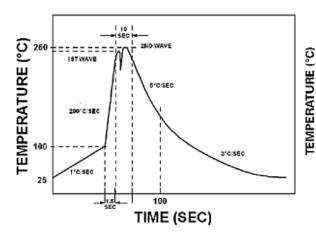
Reflow profiles in tabular form

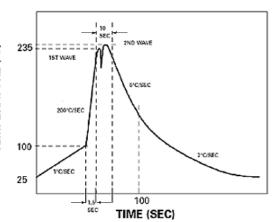
Profile Feature	Sn-Pb System	Pb-Free System
Average Ramp-Up Rate	~3°C/second	~3°C/second
Preheat – Temperature Range – Time	150-170°C 60-180 seconds	150-200°C 60-180 seconds
Time maintained above: – Temperature – Time	200°C 30-50 seconds	217°C 60-150 seconds
Peak Temperature	235°C	260°C max.
Time within +0 -5°C of actual Peak	10 seconds	40 seconds
Ramp-Down Rate	3°C/second max.	6°C/second max.

Recommended Wave Solder Profiles

The Recommended solder Profile For Devices with Pb-free terminal plating where a Pb-free solder is used

The Recommended solder Profile For Devices with Pb-free terminal plating used with leaded solder, or for devices with leaded terminal plating used with leaded solder





Wave Profiles in Tabular Form

Profile Feature	Sn-Pb System	Pb-Free System
Average Ramp-Up Rate	~200°C/second	~200°C/second
Heating rate during preheat	Typical 1-2, Max 4°C/sec	Typical 1-2, Max 4°C/Sec
Final preheat Temperature	Within 125°C of Solder Temp	Within 125°C of Solder Temp
Peak Temperature	235°C	260°C max.
Time within +0 -5°C of actual Peak	10 seconds	10 seconds
Ramp-Down Rate	5°C/second max.	5°C/second max.



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Typical Characteristic Curves

Fig 1: Collector current v/s Collector Emitter Voltage

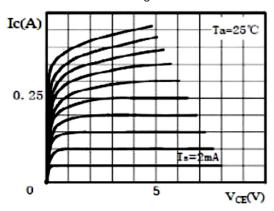


Fig 2: Collector emitter saturation voltage v/s Collector current

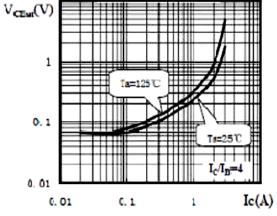


Fig 3: Power(%) v/s temperature

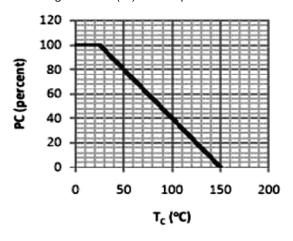


Fig 4: DC gain v/s Collector Current

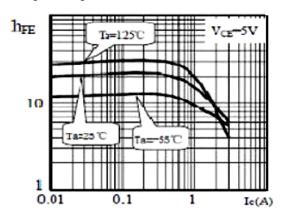


Fig 5: Base Emitter saturation voltage v/s collector current

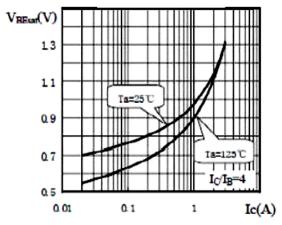
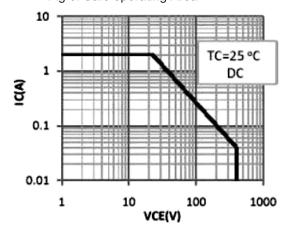


Fig 6: Safe operating Area

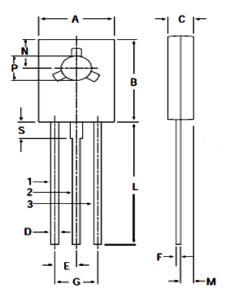






Dimensions

TO-126 Leaded Plastic Package



DIM	MIN. MAX		
Α	7.4	7.8	
В	10.5	10.8	
С	2.4	2.7	
D	0.7	0.9	
Е	2.25 TYP		
F	0.49	0.75	
G	4.5 TYP		
L	15.7 TYP		
М	1.27 TYP		
N	3.75 TYP		
Р	3	3.2	
S	2.5 TYP		

Dimensions: Millimetres

Part Number Table

Description	Part Number	
Power Transistor, Fast Switching, NPN, TO-126	CD148D	

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